

**REMARKS**

Applicants thank the Examiner for the thorough consideration given the present application. Claims 1-10, 12-22, 24-35, and 37 are currently being prosecuted. Claims 23, and 36 are canceled without prejudice to or disclaimer of the subject matter contained therein. Claims 1, 8, 9, 12, 22, 26, and 29 are amended. Claims 1, 15, and 29 are independent. Reconsideration of this application, as amended, is respectfully requested.

**Reasons for Entry of Amendments**

At the outset, it is respectfully requested that this Amendment be entered into the Official File in view of the fact that the amendments to the claims automatically place the application in condition for allowance.

In the alternative, if the Examiner does not agree that this application is in condition for allowance, it is respectfully requested that this Amendment be entered for the purpose of appeal. This Amendment reduces the issues on appeal by canceling claims 23 and 36. This Amendment was not presented at an earlier date in view of the fact that the outstanding Office Action has just now cited new grounds for rejection, and the rejection is a final rejection.

**Claim Objections**

The Examiner has objected to claim 1 because of an informality. In order to overcome this objection, claim 1 is amended herein in order to correct the

deficiencies pointed out by the Examiner. Reconsideration and withdrawal of this objection are respectfully requested.

**Rejections under 35 U.S.C. §102(e)**

Claims 1-10 and 12-37 stand rejected under 35 U.S.C. §102(e) as being anticipated by Inoue et al., U.S. Patent No. 6,127,199. This rejection is respectfully traversed.

It is respectfully submitted that independent claims 1, 15 and 29, as amended herein, set forth novel combinations of steps not taught or suggested by the references cited by the Examiner, including Inoue et al.

**Amendments to Independent Claims 1 and 15 (First and Second Embodiments)**

While not conceding the appropriateness of the independent claims 1 and 15 are amended to recite combinations of steps in a method for manufacturing a thin film transistor panel, including removing said silicon substrate by chemical mechanical polishing or an etching process.

The above limitation was previously set forth in claims 8, 9 and 22, 23, respectively. See also FIGS. 1H and 4G, and page 9, lines 22-24 of the specification.

It is respectfully submitted that the combinations of method steps set forth in independent claims 1 and 15 are not anticipated by Inoue et al., and that in contrast to the present invention, Inoue et al. (column 17, line 36-39, and FIG.

13) merely discloses substrate 3000 being irradiated with an excimer laser light from the back thereof, and then is exfoliated. Inoue et al. removes the silicon substrate by laser light, and thus the Inoue et al. silicon substrate must be a transparent electrode. Since the present application removes the silicon substrate by chemical mechanical polishing or an etching process, the silicon substrate of the present application may be either transparent or not.

The Examiner will note that dependent claims 8 and 22 are amended herein to recite the silicon substrate 10 is non-transparent. Support can be found on page 7, line 21, and page 9, line 23 of the specification. Inoue et al. fail to teach silicon substrate that is non-transparent

The Examiner will also note that dependent claim 9 is amended herein to recite further comprising the step of forming metal contacts after said plurality of transparent electrodes are formed. Support for this limitation can be seen in FIGS. 1B and 1D, which clearly shows transparent electrode 18 being formed before metal contact layer 24, respectfully. By contrast, Inoue et al. teach forming transparent electrode after metal contacts are formed.

In view of the above amendments and arguments, independent claims 1 and 15, and the claims depending therefrom, are in condition for allowance.

**Amendments to Independent Claim 29 (Third Embodiment)**

Independent claim 29 is amended herein to recite novel combinations of method steps not taught or suggested in the cited art.

Specifically, claim 29 is amended herein to recite a combination of steps directed to method for manufacturing a thin film transistor panel including the step of forming said thin film transistor structures further comprises: forming a source region and a drain region on said crystal silicon thin film; forming a gate insulator on said crystal silicon thin film; forming a gate electrode on said gate insulator; forming an interlayer on said gate electrode and said gate insulator; and forming a metal contact layer on said interlayer.

The above limitations were previously set forth in dependent claim 36, which is canceled. Support for presently amended claim 29 can also be found, e.g., at page 11, lines 3-8, of the specification and in FIG. 5D.

The Applicant respectfully submit that Inoue et al. fail to teach or suggest the step of forming said thin film transistor structures further comprises: forming a source region and a drain region on said crystal silicon thin film; forming a gate insulator on said crystal silicon thin film; forming a gate electrode on said gate insulator; forming an interlayer on said gate electrode and said gate insulator; and forming a metal contact layer on said interlayer.

In view of the above amendments and arguments, independent claim 29, and the claims depending therefrom, are in condition for allowance.

In summary, it is respectfully submitted that Inoue et al. fail to anticipate or disclose the present invention, and reconsideration and withdrawal of the

rejections are respectfully requested. Independent claims 1, 15, and 29, and the claims depending therefrom, are in condition for allowance.

**CONCLUSION**

All of the stated grounds of rejection have been properly traversed, accommodated, or rendered moot. Applicants, therefore, respectfully request that the Examiner reconsider the outstanding rejections and that they be withdrawn. It is believed that a full and complete response has been made to the outstanding Office Action, and that the present application is in condition for allowance.

However, in the event that any outstanding matters remain, the Examiner is invited to telephone the undersigned at (703) 205-8000.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies to charge payment or credit any overpayment to Deposit Account No. 02-2448 for any additional fees required under 37 C.F.R. §§1.16 or 1.17, particularly extension of time fees.

Respectfully submitted,

BIRCH, STEWART, KOLASCH & BIRCH, LLP

By Joe McKinney Muncy  
Joe McKinney Muncy  
Reg. No. 32,334

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Attachment  
KM/CTT:jls  
CTT

P. O. Box 747  
Falls Church, VA 22040-0747  
(703) 205-8000